

TECHNICAL DATA DATA SHEET 317, REV -

HERMETIC POWER MOSFET N-CHANNEL

FEATURES:

- 100 Volt, 0.16 Ohm, 14A MOSFET
- Fast Switching
- Low R_{DS (on)}
- Equivalent to IRF130 Series

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_c = 25^{\circ}$ C UNLESS OTHERWISE SPECIFIED.

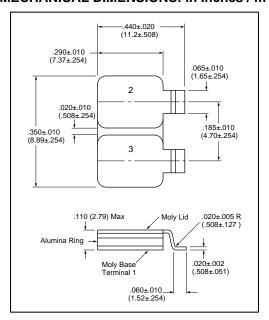
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
ON-STATE DRAIN CURRENT @ $T_C = 100$ °C	I _D	-	-	14	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	°C
TOTAL DEVICE DISSIPATION @ T _C = 25°C	P_{D}	-	-	96	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	R_{thJC}	-	-	1.3	°C/W

ELECTRICAL CHARACTERISTICS

$\begin{array}{c ccccccccccccccccccccccccccccccccccc$							
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			BV_{DSS}	100	-	-	Volts
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$V_{GS} =$	$0V, I_D = 1.0mA$					
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	DRAIN TO SOURCE ON-STATE VOLTAGE	ΞE	$V_{DS(ON)}$	-		100	Volts
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V_{GS}	$= 10V, I_D = 10A$, ,				
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	STATIC DRAIN TO SOURCE ON STATE	RESISTANCE	R _{DS(ON)}	-	0.14	0.16	Ω
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$V_{GS} = 10V, I_{D} = 2$	20A	,				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	GATE THRESHOLD VOLTAGE V _{DS} = V	V_{GS} , $I_{D} = 250 \mu A$	$V_{GS(th)}$	2.0	2.8	4.0	Volts
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	FORWARD TRANSCONDUCTANCE			4.6	7.0	-	S(1/Ω)
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$V_{DS} \ge I_{D (ON)} X, R_{DS (ON)} Max$	$x., I_{DS} = 0.6 X I_{D}$					
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	ZERO GATE VOLTAGE DRAIN CURREN	Т		-	-		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$V_{DS} = Max. Rating, V_{GS} = 0V$		I_{DSS}			250	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$V_{DS} = 0.8xMax$. Rating, $V_{GS} =$	$0V, T_J = 125^{\circ}C$				1000	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	GATE TO SOURCE LEAKAGE FORWARI	$V_{GS} = 20V$	I_{GSS}	-	-	100	nA
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	GATE TO SOURCE LEAKAGE REVERSE	$V_{GS} = -20V$				-100	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	TURN ON DELAY TIME	$V_{DD} = 50V$,	t _{d(ON)}	-	9.5	14	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	RISE TIME	$I_D = 7.0A$,	`t _r		42	63	nsec
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	TURN OFF DELAY TIME	$R_G = 12\Omega$,	$t_{d(OFF)}$		22	33	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	FALL TIME	$V_{GS} = 10V$			25	38	
REVERSE RECOVERY TIME $T_J = 25^{\circ}C, \qquad t_{rr} \qquad - \qquad - \qquad 250$ $I_f = 14A, \qquad \qquad di_f/ds = 100A/\mu sec,$ $INPUT CAPACITANCE \qquad V_{GS} = 0 \ V \qquad C_{iss} \qquad - \qquad 650 \qquad - \qquad 0$ $OUTPUT CAPACITANCE \qquad V_{DS} = 25 \ V \qquad C_{oss} \qquad 240 \qquad pF$	DIODE FORWARD VOLTAGE $T_C = 2$	25°C, I _S = 14A,	V_{SD}	-	1.0	2.5	Volts
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		$V_{GS} = 0V$					
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	REVERSE RECOVERY TIME	$T_{J} = 25^{\circ}C$	t _{rr}	-	-	250	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$							nsec
OUTPUT CAPACITANCE V _{DS} = 25 V C _{oss} 240 pF	di _F /c	ds = 100A/μsec,					
= 7			C _{iss}	-	650	-	
	OUTPUT CAPACITANCE	$V_{DS} = 25 \text{ V}$	C_{oss}		240		pF
	REVERSE TRANSFER CAPACITANCE	f = 1.0MHz			44		-

DATA SHEET 317 REVISION -

MECHANICAL DIMENSIONS: in Inches / m



SHD-4A

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
N-CHANNEL MOSFET	DRAIN	SOURCE	GATE
SHD-4A PACKAGE			

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